

### General Description

The WSR110N20 is the highest performance trench N-Channel MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the device is suitable for use as a Battery protection or in other Switching application.

The WSR110N20 meet the RoHS and GreenProduct requirement 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

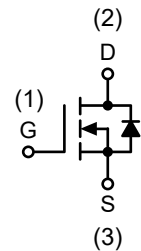
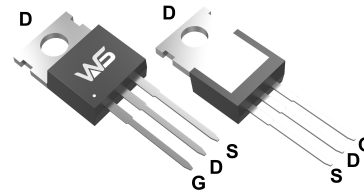
### Product Summary

| BV <sub>DSS</sub> | R <sub>DSON</sub> | I <sub>D</sub> |
|-------------------|-------------------|----------------|
| 200V              | 9.2mΩ             | 110A           |

### Applications

- DC Motor Driver
- Synchronous Rectification in DC/DC
- AC/DC Converters

### TO-220-3L Pin Configuration



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| Symbol                                | Parameter  | Rating     | Units |
|---------------------------------------|--|------------|-------|
| V <sub>DS</sub>                       | Drain-Source Voltage   | 200        | V     |
| V <sub>GS</sub>                       | Gate-Source Voltage  | ±20        | V     |
| I <sub>D</sub> @T <sub>C</sub> =25°C  | Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>3</sup> | 110        | A     |
| I <sub>D</sub> @T <sub>C</sub> =100°C | Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>3</sup> | 49         | A     |
| I <sub>DM</sub>                       | Pulsed Drain Current <sup>2</sup> T <sub>C</sub> =25°C       | 332        | A     |
| P <sub>D</sub> @T <sub>C</sub> =25°C  | Total Power Dissipation                                      | 166.7      | W     |
| T <sub>STG</sub>                      | Storage Temperature Range                                    | -55 to 150 | °C    |
| T <sub>J</sub>                        | Operating Junction Temperature Range                         | -55 to 150 | °C    |

### Thermal Resistance Ratings

| Symbol           | Parameter  | Typ. | Max. | Unit |
|------------------|--|------|------|------|
| R <sub>θJA</sub> | Thermal Resistance Junction-Ambient <sup>1</sup> | ---  | 62.5 | °C/W |
| R <sub>θJC</sub> | Thermal Resistance Junction-Case                 | ---  | 0.75 | °C/W |

**Electrical Characteristics**

| Symbol       | Parameter                         | Conditions  | Min. | Typ.  | Max.      | Unit       |
|--------------|-----------------------------------|---|------|-------|-----------|------------|
| $BV_{DSS}$   | Drain-Source Breakdown Voltage    | $V_{GS}=0V, I_D=250\mu A$                         | 200  | ---   | ---       | V          |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS}=10V, I_D=30A$                             | ---  | 9.2   | 12        | m $\Omega$ |
| $V_{GS(th)}$ | Gate Threshold Voltage            | $V_{GS}=V_{DS}, I_D=250\mu A$                     | 2.0  | 3.0   | 4.0       | V          |
| $I_{DSS}$    | Drain-Source Leakage Current      | $V_{DS}=160V, V_{GS}=0V, T_J=25^\circ C$          | ---  | ---   | 1         | $\mu A$    |
| $I_{GSS}$    | Gate-Source Leakage Current       | $V_{GS}=\pm 20V, V_{DS}=0V$                       | ---  | ---   | $\pm 100$ | nA         |
| $Q_g$        | Total Gate Charge                 | $V_{DS}=100V, V_{GS}=10V, I_D=55A$                | ---  | 146   | ---       | nC         |
| $Q_{gs}$     | Gate-Source Charge                |   | ---  | 50    | ---       |            |
| $Q_{gd}$     | Gate-Drain Charge                 |   | ---  | 28    | ---       |            |
| $T_{d(on)}$  | Turn-On Delay Time                | $V_{DD}=100V, I_D=55A, R_G=4.7\Omega, V_{GS}=10V$ | ---  | 22    | ---       | ns         |
| $T_r$        | Rise Time                         |   | ---  | 47    | ---       |            |
| $T_{d(off)}$ | Turn-Off Delay Time               |   | ---  | 19    | ---       |            |
| $T_f$        | Fall Time                         |   | ---  | 89    | ---       |            |
| $C_{iss}$    | Input Capacitance                 | $V_{DS}=50V, V_{GS}=0V, f=1MHz$                   | ---  | 10700 | ---       | pF         |
| $C_{oss}$    | Output Capacitance                |   | ---  | 390   | ---       |            |
| $C_{rss}$    | Reverse Transfer Capacitance      |   | ---  | 70    | ---       |            |

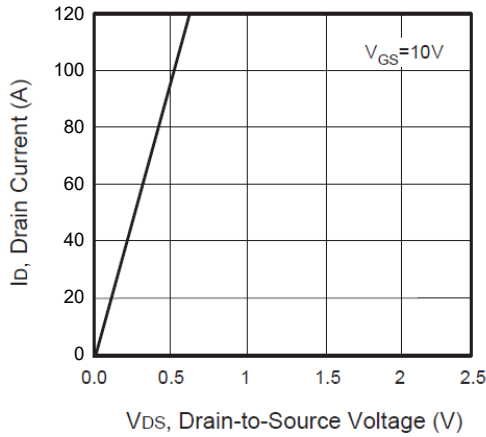
**Diode Characteristics**

| Symbol   | Parameter                 | Conditions                          | Min. | Typ. | Max. | Unit |
|----------|---------------------------|-------------------------------------|------|------|------|------|
| $I_S$    | Continuous Source Current | $V_G=V_D=0V$ , Force Current        | ---  | ---  | 83   | A    |
| $V_{SD}$ | Diode Forward Voltage     | $V_{GS}=0V, I_S=1A, T_J=25^\circ C$ | ---  | ---  | 1.2  | V    |

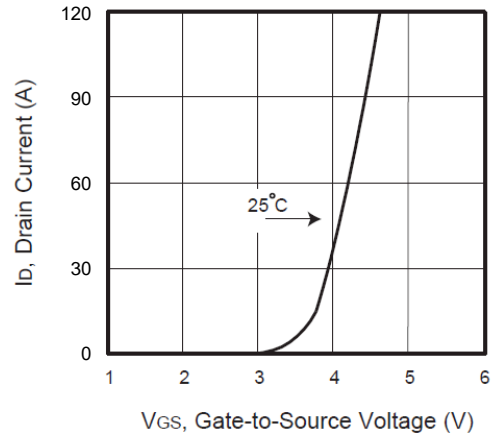
Note :

1. The value of  $R_{thJA}$  is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with  $T_G=25^\circ C$ . The value in any given application depends on the user's specific board design.
2. Repetitive rating, pulse width limited by junction temperature.
3. The current rating is based on the  $\leq 10s$  junction to ambient thermal resistance rating.
4. Pulse Test: Pulse Wide  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .

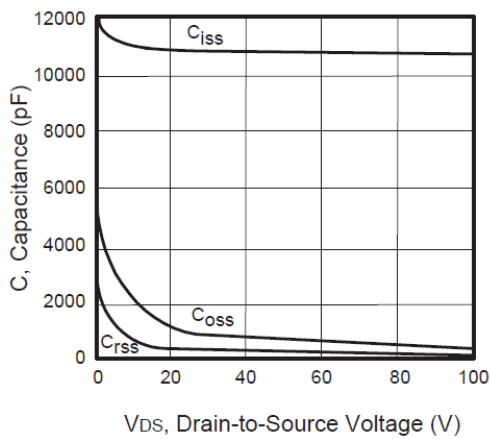
**Typical Characteristics**



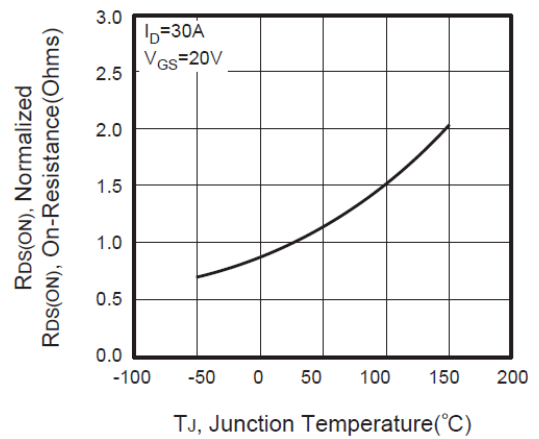
**Figure 1. Output Characteristics**



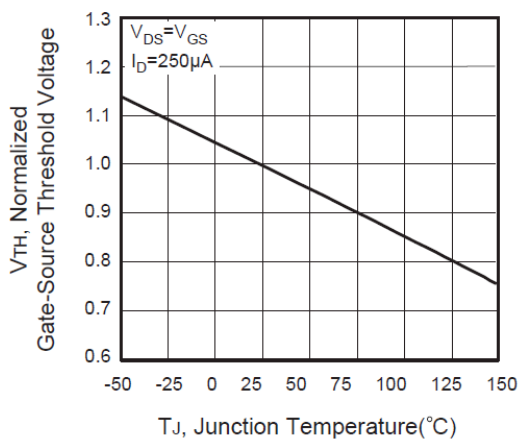
**Figure 2. Transfer Characteristics**



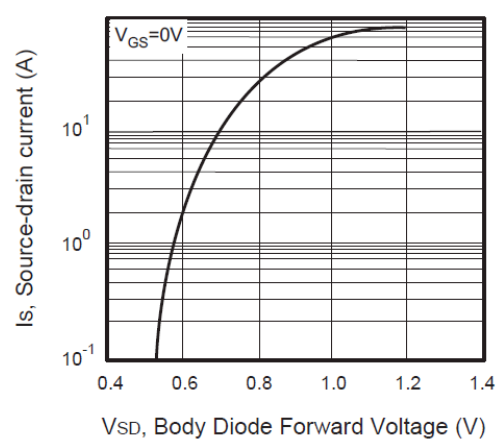
**Figure 3. Capacitance**



**Figure 4. On-Resistance Variation with Temperature**



**Figure 5. Gate Threshold Variation with Temperature**



**Figure 6. Body Diode Forward Voltage Variation with Source Current**

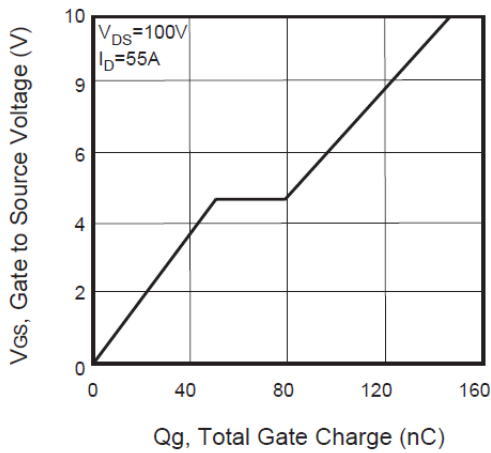


Figure 7. Gate Charge

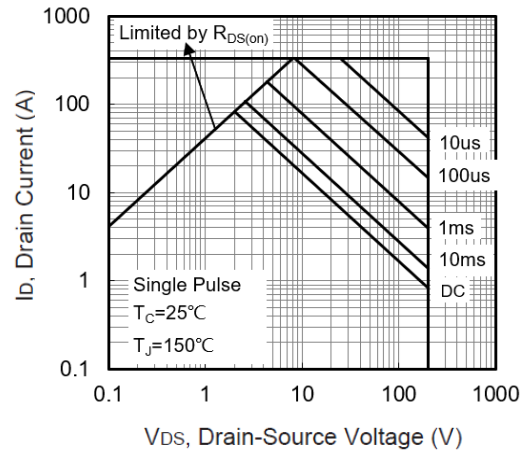


Figure 8. Maximum Safe Operating Area

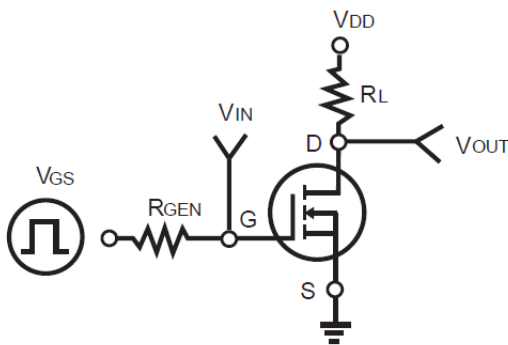


Figure 9. Switching Test Circuit

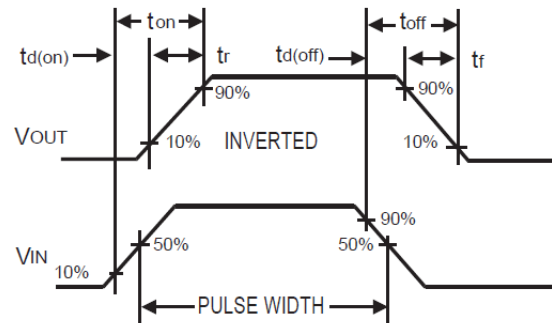


Figure 10. Switching Waveforms

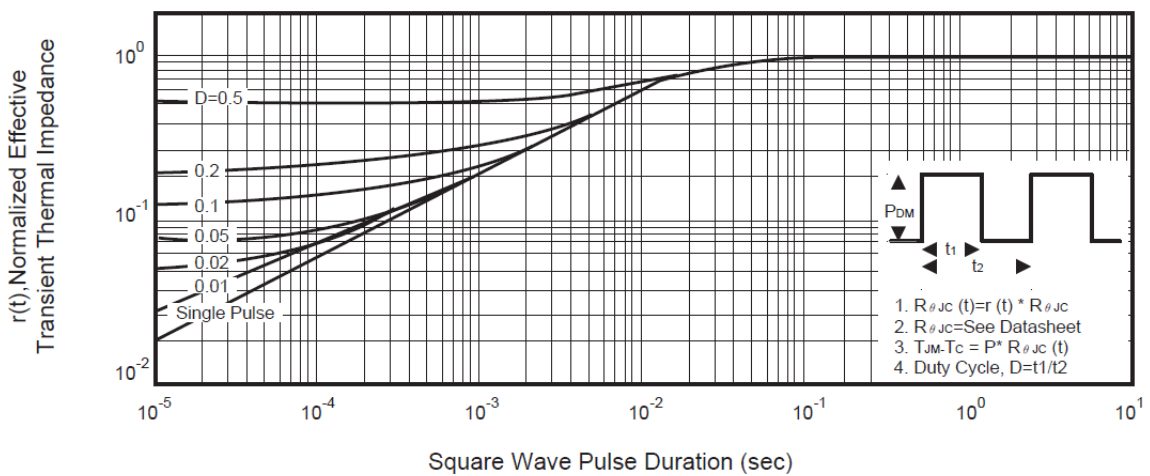
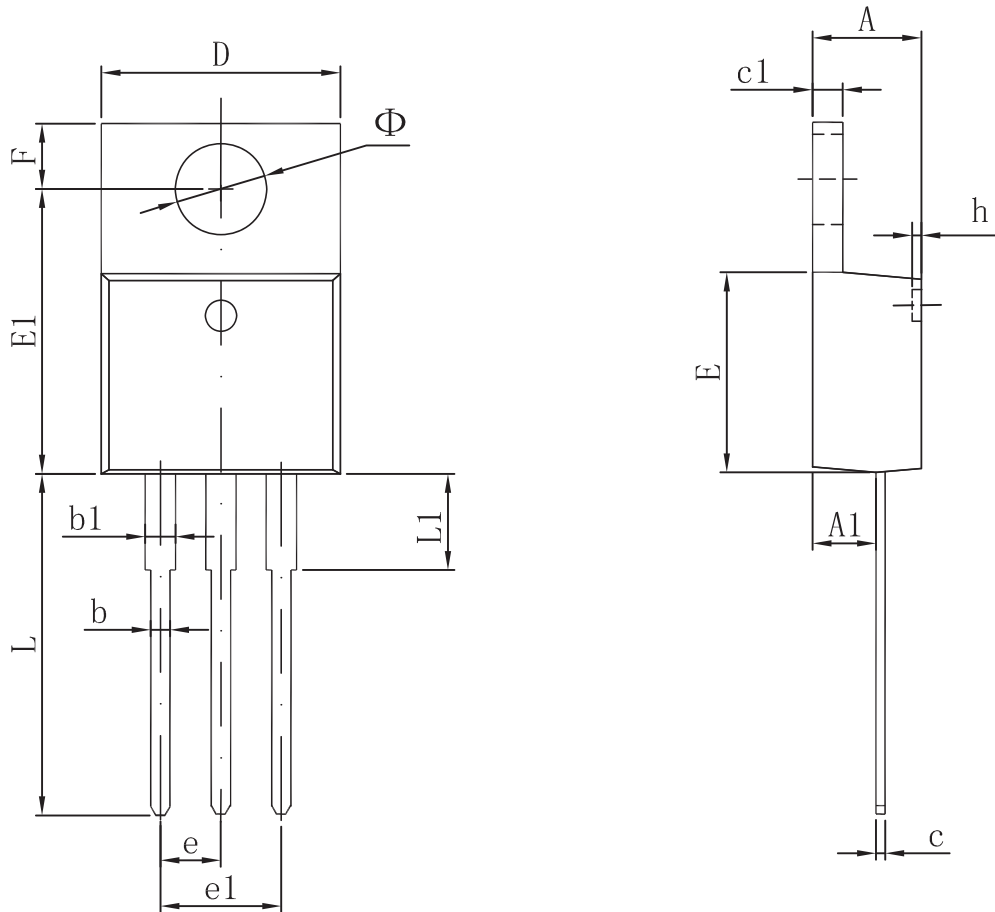


Figure 11. Normalized Thermal Transient Impedance Curve

**Packaging information**


| Symbol | Dimensions In Millimeters |        | Dimensions In Inches |       |
|--------|---------------------------|--------|----------------------|-------|
|        | Min                       | Max    | Min                  | Max   |
| A      | 4.470                     | 4.670  | 0.176                | 0.184 |
| A1     | 2.520                     | 2.820  | 0.099                | 0.111 |
| b      | 0.710                     | 0.910  | 0.028                | 0.036 |
| b1     | 1.170                     | 1.370  | 0.046                | 0.054 |
| c      | 0.310                     | 0.530  | 0.012                | 0.021 |
| c1     | 1.170                     | 1.370  | 0.046                | 0.054 |
| D      | 10.010                    | 10.310 | 0.394                | 0.406 |
| E      | 8.500                     | 8.900  | 0.335                | 0.350 |
| E1     | 12.060                    | 12.460 | 0.475                | 0.491 |
| e      | 2.540 TYP                 |        | 0.100 TYP            |       |
| e1     | 4.980                     | 5.180  | 0.196                | 0.204 |
| F      | 2.590                     | 2.890  | 0.102                | 0.114 |
| h      | 0.000                     | 0.300  | 0.000                | 0.012 |
| L      | 13.400                    | 13.800 | 0.528                | 0.543 |
| L1     | 3.560                     | 3.960  | 0.140                | 0.156 |
| Φ      | 3.735                     | 3.935  | 0.147                | 0.155 |



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